



EECS 151/251A
Fall 2017
Digital Design and
Integrated Circuits

Instructors:
Weaver and Wawrzynek

Lecture 8

Administration

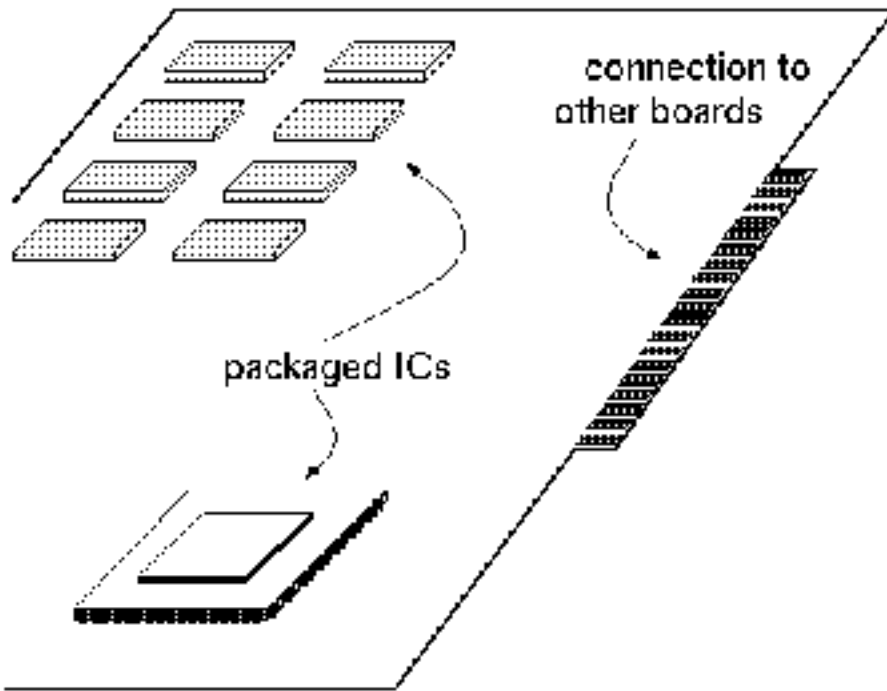
- Exam in One Week
 - Take here in class and with an extra 30 minutes (5:30-7:30).
 - Covers topics: beginning through 2/6.

Overview of Physical Implementations

The stuff out of which we make systems.

- Integrated Circuits (ICs)
 - Combinational logic circuits, memory elements, analog interfaces.
- Printed Circuits (PC) boards
 - substrate for ICs and interconnection, distribution of CLK, Vdd, and GND signals, heat dissipation.
- Power Supplies
 - Converts line AC voltage to regulated DC low voltage levels.
- Chassis (rack, card case, ...)
 - holds boards, power supply, fans, provides physical interface to user or other systems.
- Connectors and Cables.

Printed Circuit Boards

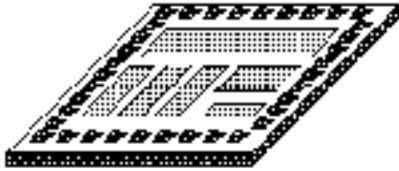


- ❑ fiberglass or ceramic
- ❑ 1-25 conductive layers
- ❑ ~1-20in on a side
- ❑ IC packages are soldered down.

Multichip Modules (MCMs)

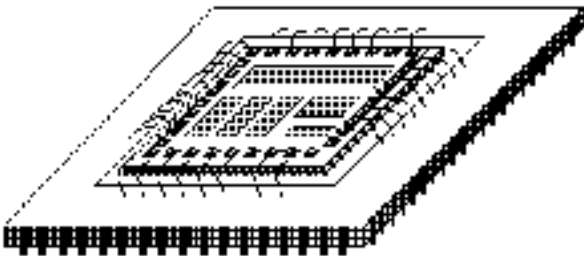
- Multiple chips directly connected to a substrate. (silicon, ceramic, plastic, fiberglass) without chip packages.

Integrated Circuits



- ❑ Primarily Crystalline Silicon
- ❑ 1mm - 25mm on a side
- ❑ 100 - 20B transistors
- ❑ (25 - 250M “logic gates”)
- ❑ 3 - 10 conductive layers
- ❑ 2018 state-of-the-art feature size
 $7\text{nm} = 0.007 \times 10^{-6} \text{ m}$
- ❑ “CMOS” most common -
complementary metal oxide
semiconductor

Chip in Package



- Package provides:
 - spreading of chip-level signal paths to board-level
 - heat dissipation.
- Ceramic or plastic with gold

From Gates to Circuits



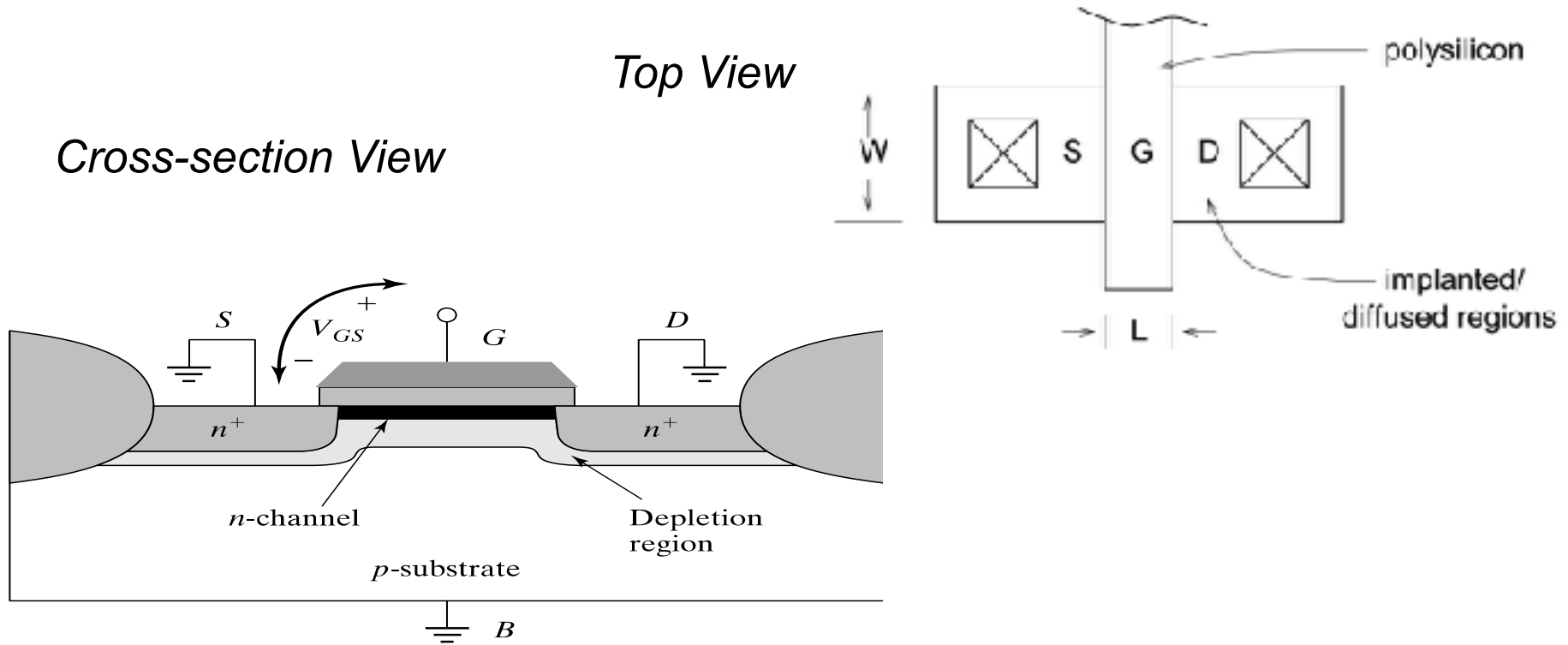
- ❑ Digital abstraction
- ❑ CMOS abstraction
- ❑ Switch logic
- ❑ Transient properties



CMOS abstraction

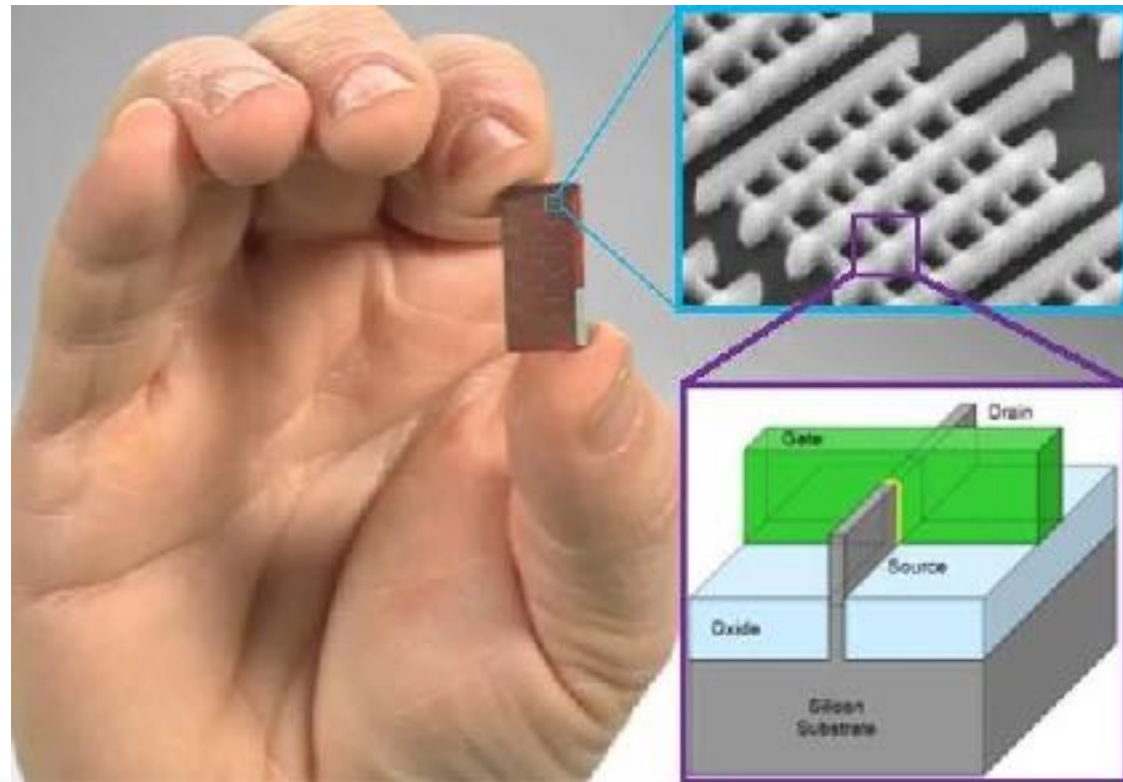
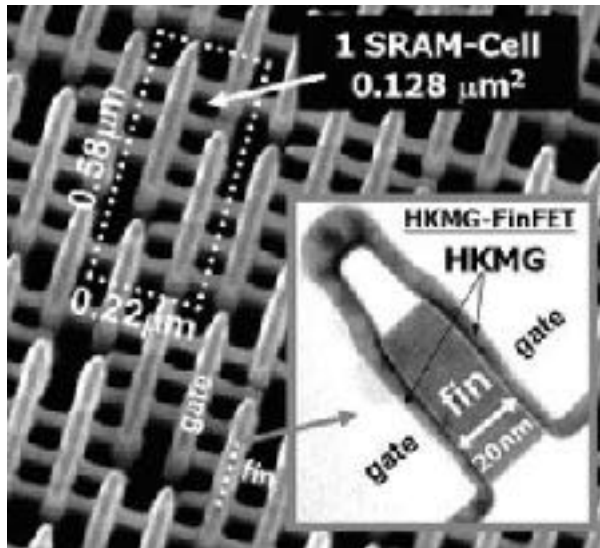
CMOS Devices

- MOSFET (Metal Oxide Semiconductor Field Effect Transistor).



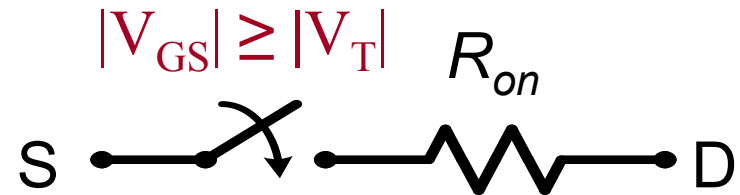
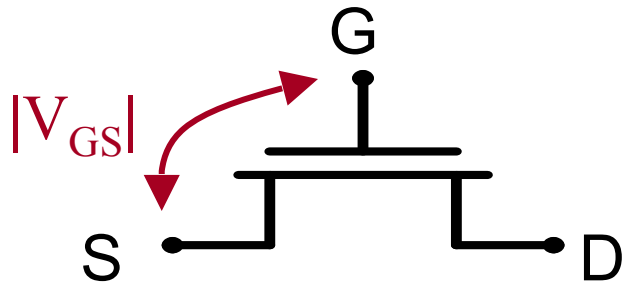
The gate acts like a capacitor. A high voltage on the gate attracts charge into the channel. If a voltage exists between the source and drain a current will flow. In its simplest approximation, the device acts like a switch.

CMOS Transistors – State-of-the-Art

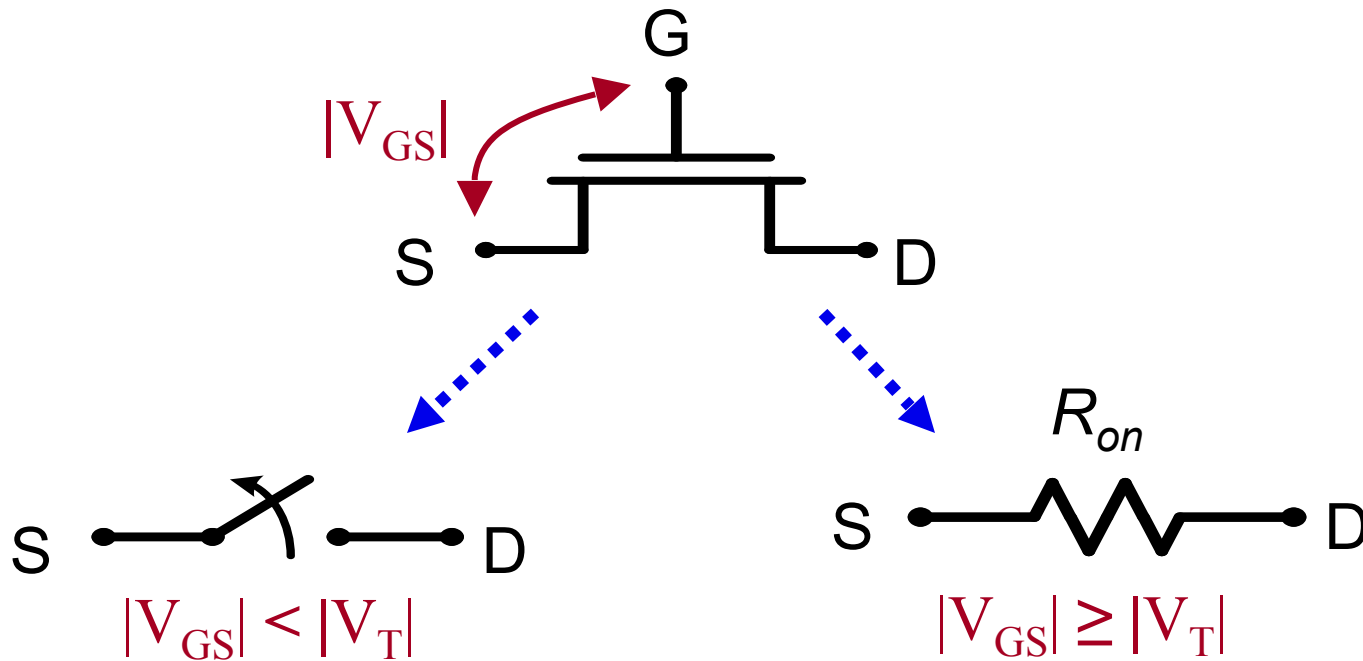


MOS Transistor as a Switch

MOS Transistor \leftrightarrow A Switch!



ON/OFF Switch Model of MOS Transistor

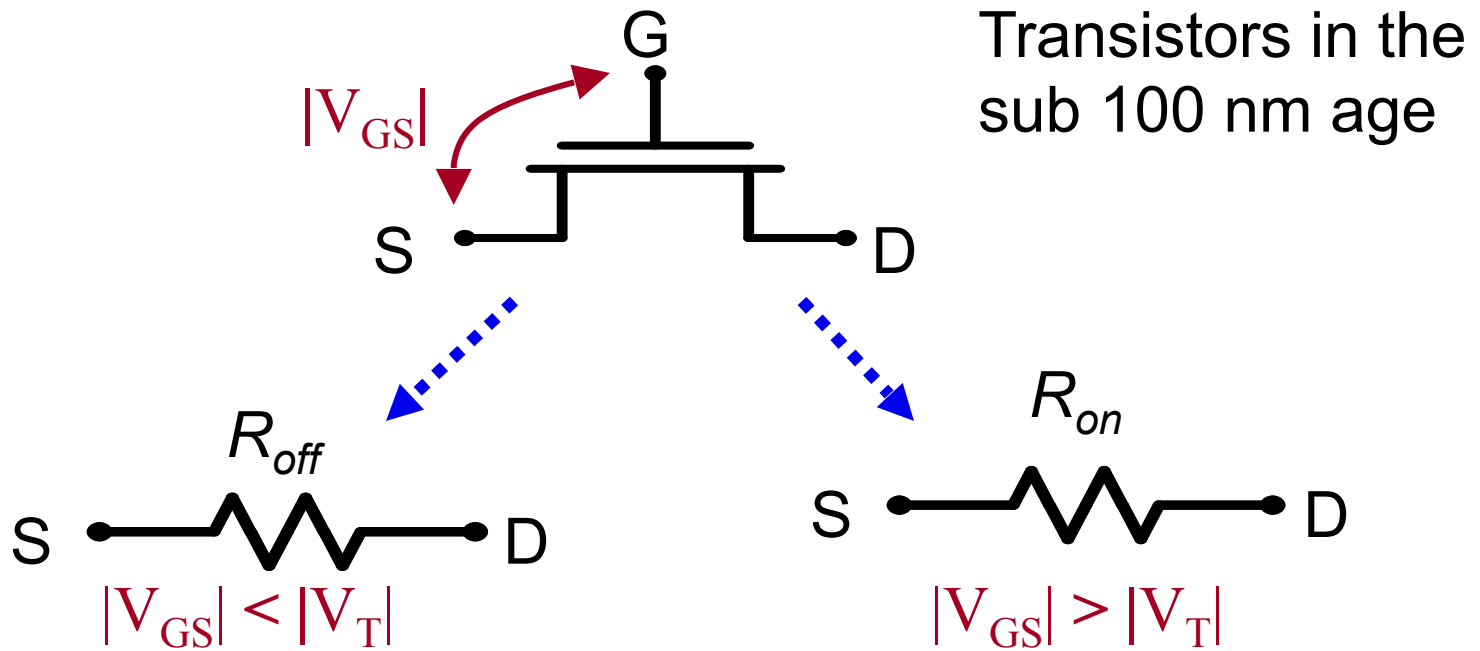


Drain versus Source - Definition

*MOS transistors are symmetrical devices
(Source and drain are interchangeable)*

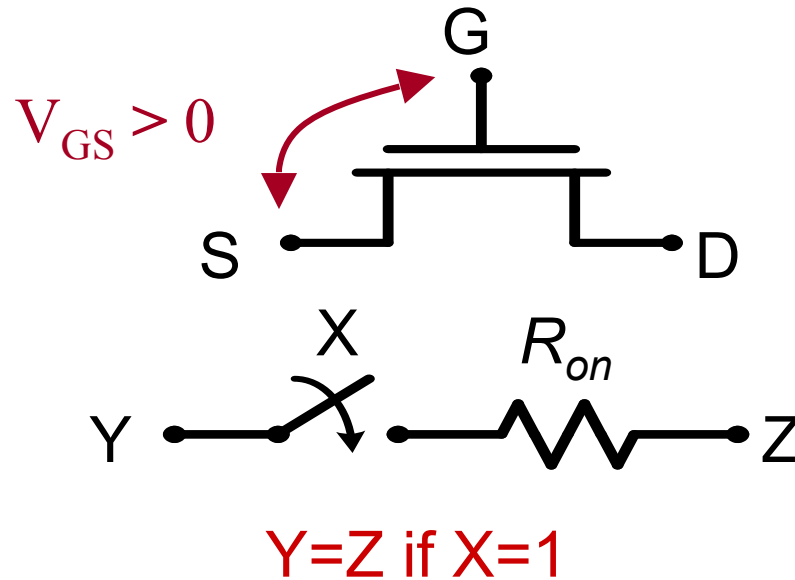
Source is the node w/ the lowest voltage

A More Realistic Switch

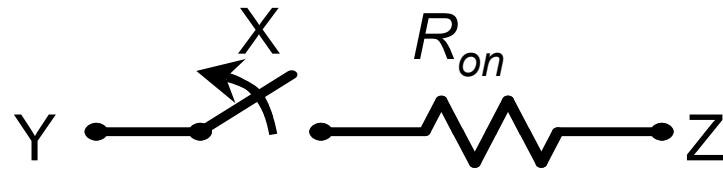


A Logic Perspective

NMOS Transistor

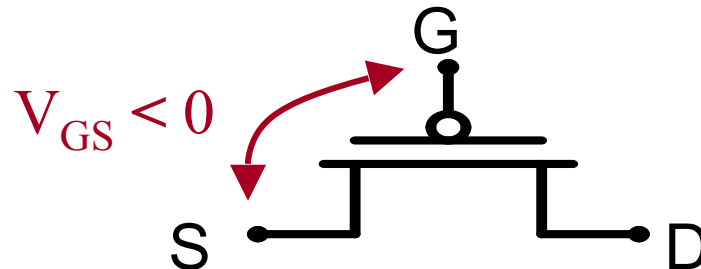


A Complementary Switch



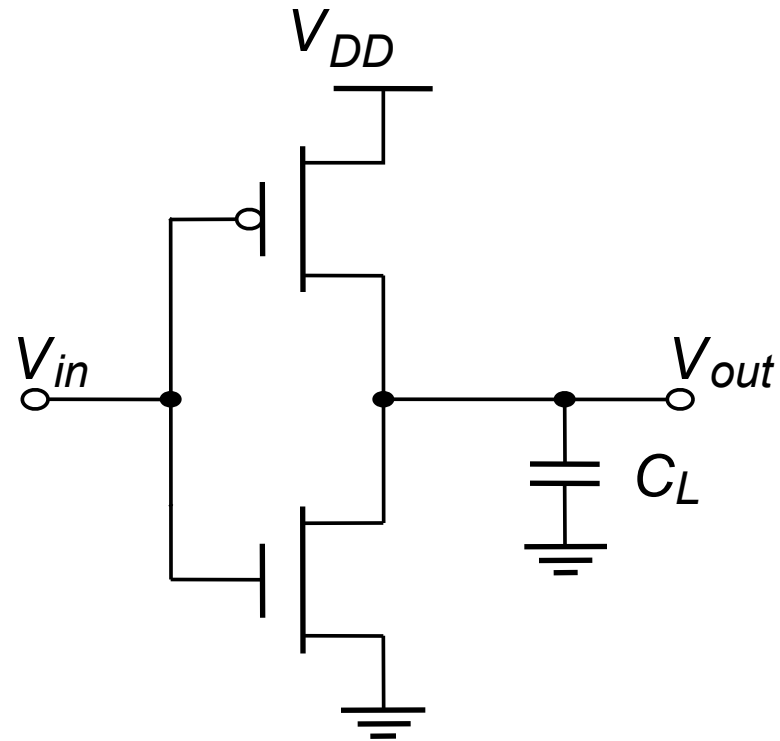
$Y=Z$ if $X=0$

PMOS Transistor



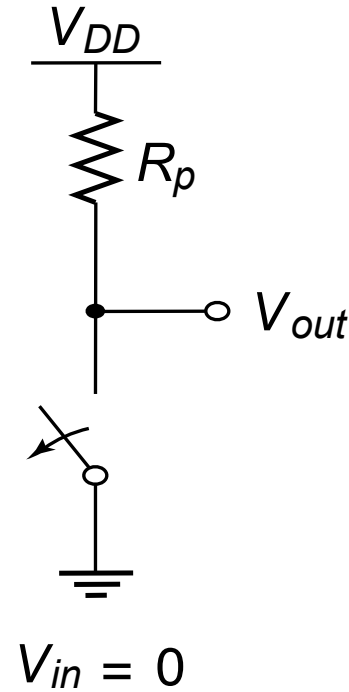
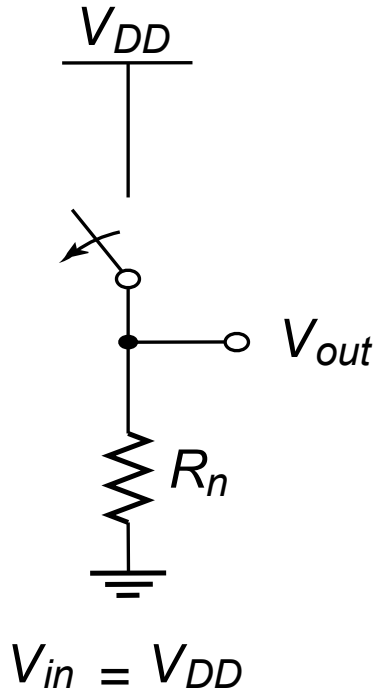
Source is the node w/ the highest voltage!

The CMOS Inverter: A First Glance



The Switch Inverter

First-Order DC Analysis



$$\begin{aligned} V_{OL} &= 0 \\ V_{OH} &= V_{DD} \\ V_M &= f(R_n, R_p) \end{aligned}$$



Switch logic

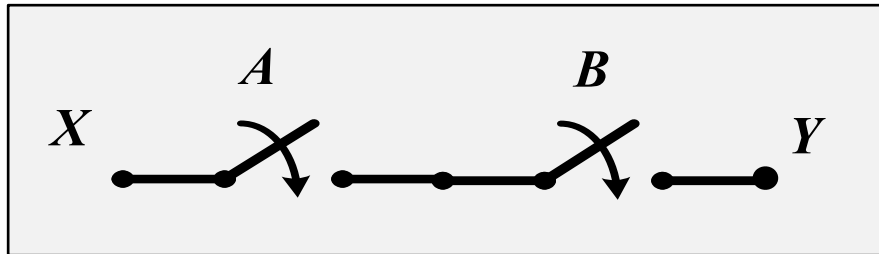
Static Logic Gate

- At every point in time (except during the switching transients) each gate output is connected to either V_{DD} or V_{SS} via a low resistive path.
- The output of the gate assumes at all times the value of the Boolean function implemented by the circuit (ignoring, once again, the transient effects during switching periods).

Example: CMOS Inverter

Building logic from switches

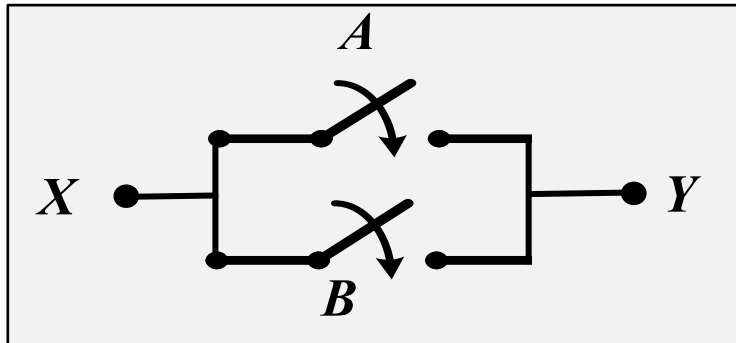
Series



AND

$Y = X$ if A AND B

Parallel



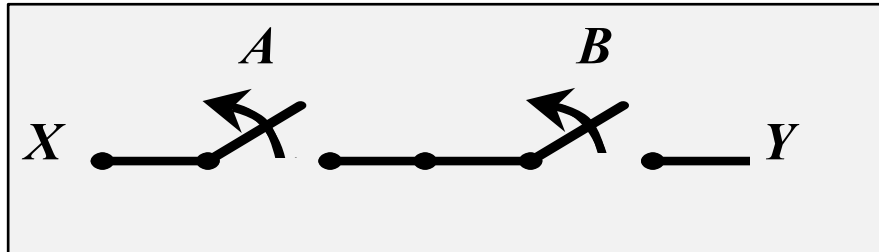
OR

$Y = X$ if A OR B

(output undefined if condition not true)

Logic using inverting switches

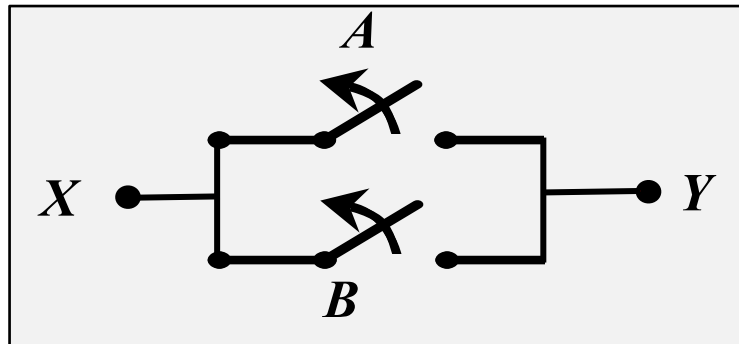
Series



NOR

$$Y = X \text{ if } \bar{A} \text{ AND } \bar{B} \\ = \overline{A + B}$$

Parallel

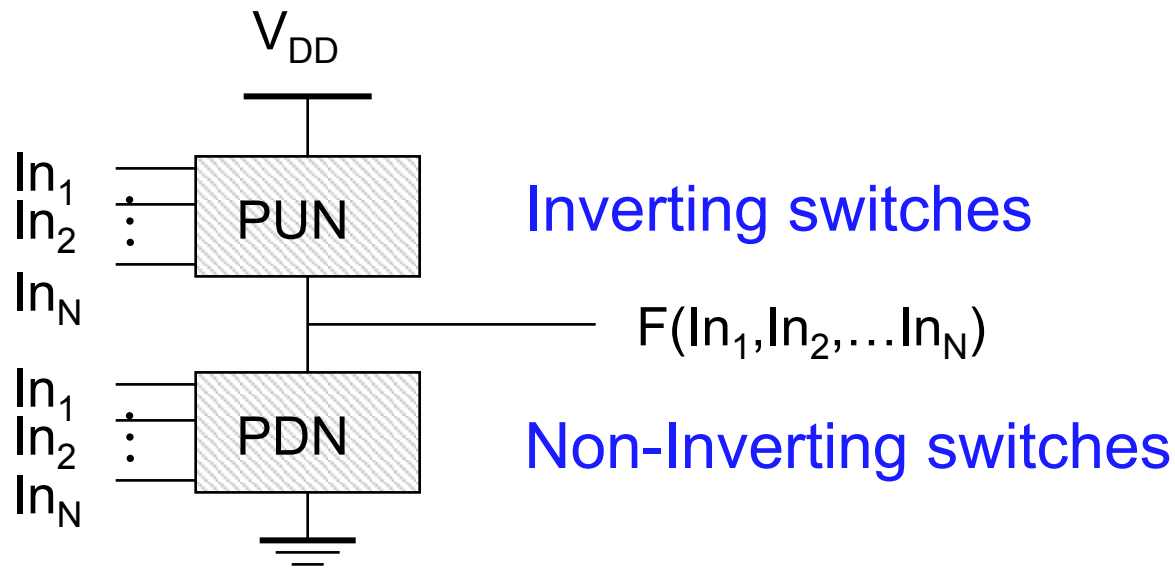


NAND

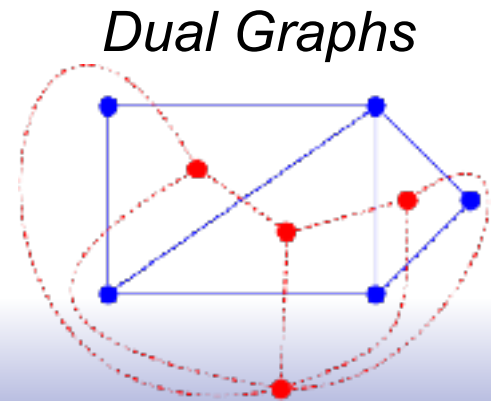
$$Y = X \text{ if } \bar{A} \text{ OR } \bar{B} \\ = \overline{AB}$$

(output undefined if condition not true)

Static Complementary CMOS



PUN and PDN are **dual** logic networks
PUN and PDN functions are **complementary**



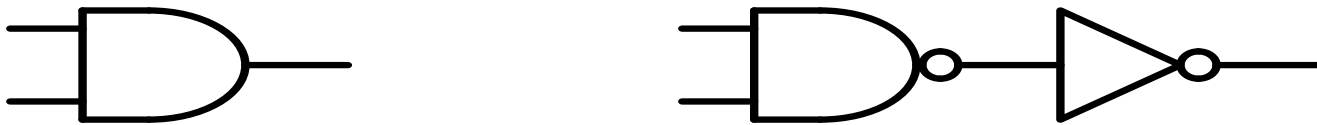
Complementary CMOS Logic Style

- PUN is the **dual** to PDN
(can be shown using DeMorgan's Theorems)

$$\overline{A + B} = \overline{A} \overline{B}$$

$$\overline{A B} = \overline{A} + \overline{B}$$

- Static CMOS gates are always inverting

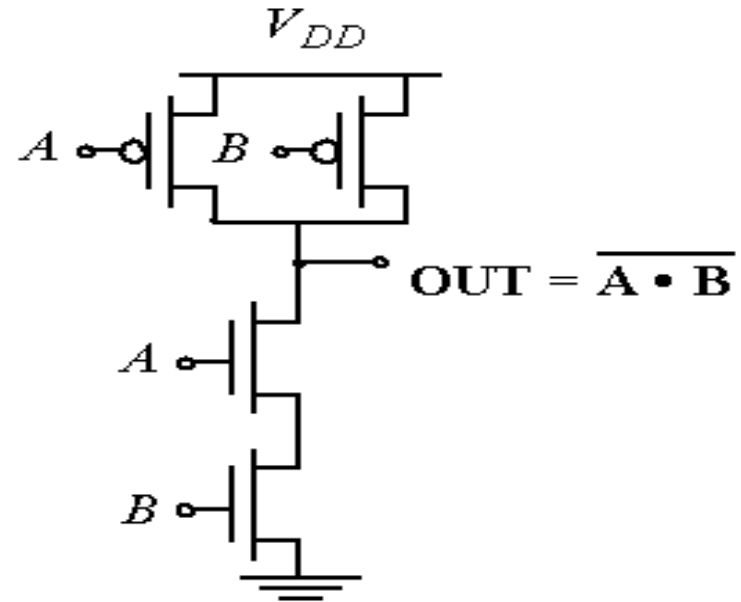


AND = NAND + INV

Example Gate: NAND

| A | B | Out |
|---|---|-----|
| 0 | 0 | 1 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

Truth Table of a 2 input NAND gate

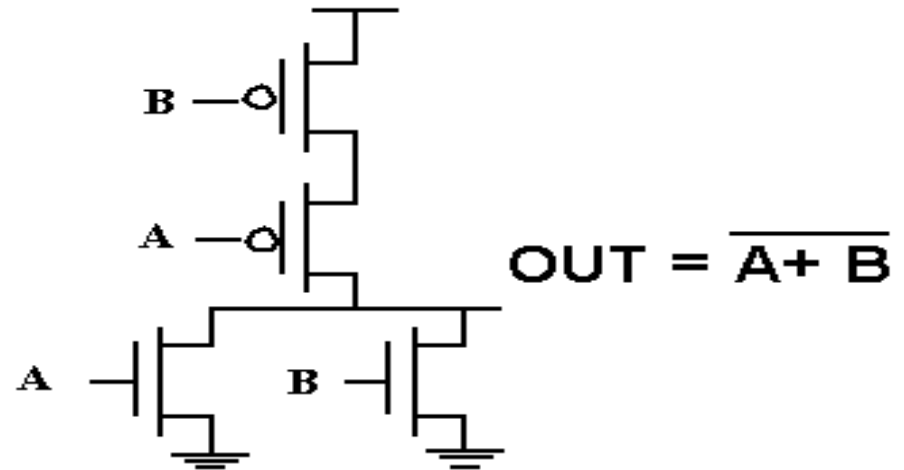


- PDN: $G = AB \Rightarrow$ Conduction to GND
- PUN: $F = \overline{A} + \overline{B} = \overline{AB} \Rightarrow$ Conduction to V_{DD}
- $\overline{G(In_1, In_2, In_3, \dots)} \equiv F(\overline{In_1}, \overline{In_2}, \overline{In_3}, \dots)$

Example Gate: NOR

| A | B | Out |
|---|---|-----|
| 0 | 0 | 1 |
| 0 | 1 | 0 |
| 1 | 0 | 0 |
| 1 | 1 | 0 |

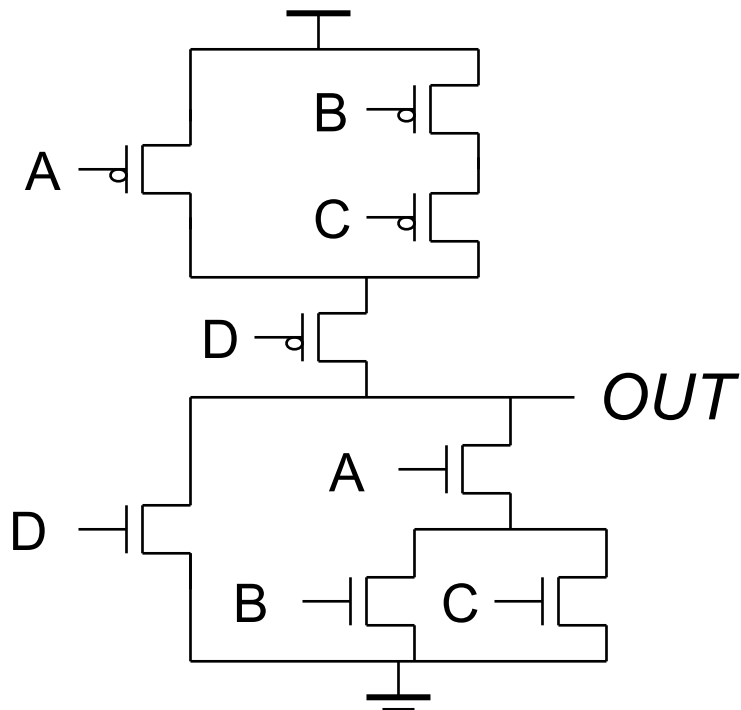
Truth Table of a 2 input NOR gate



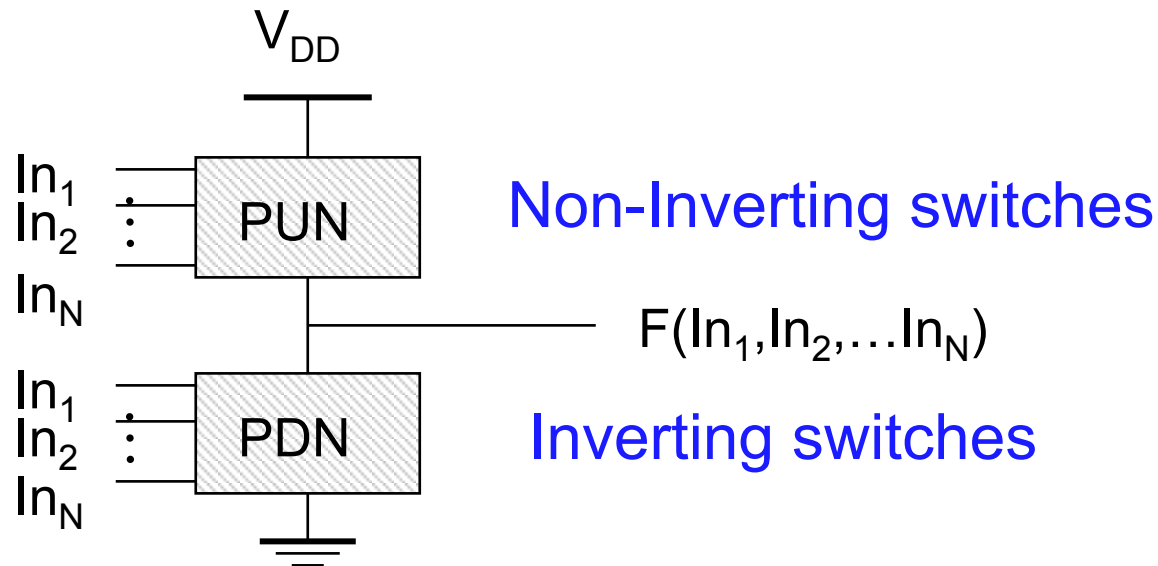
Complex CMOS Gate

$$\text{OUT} = \overline{D + A \cdot (B + C)}$$

$$\text{OUT} = \overline{D \cdot A + B \cdot C}$$



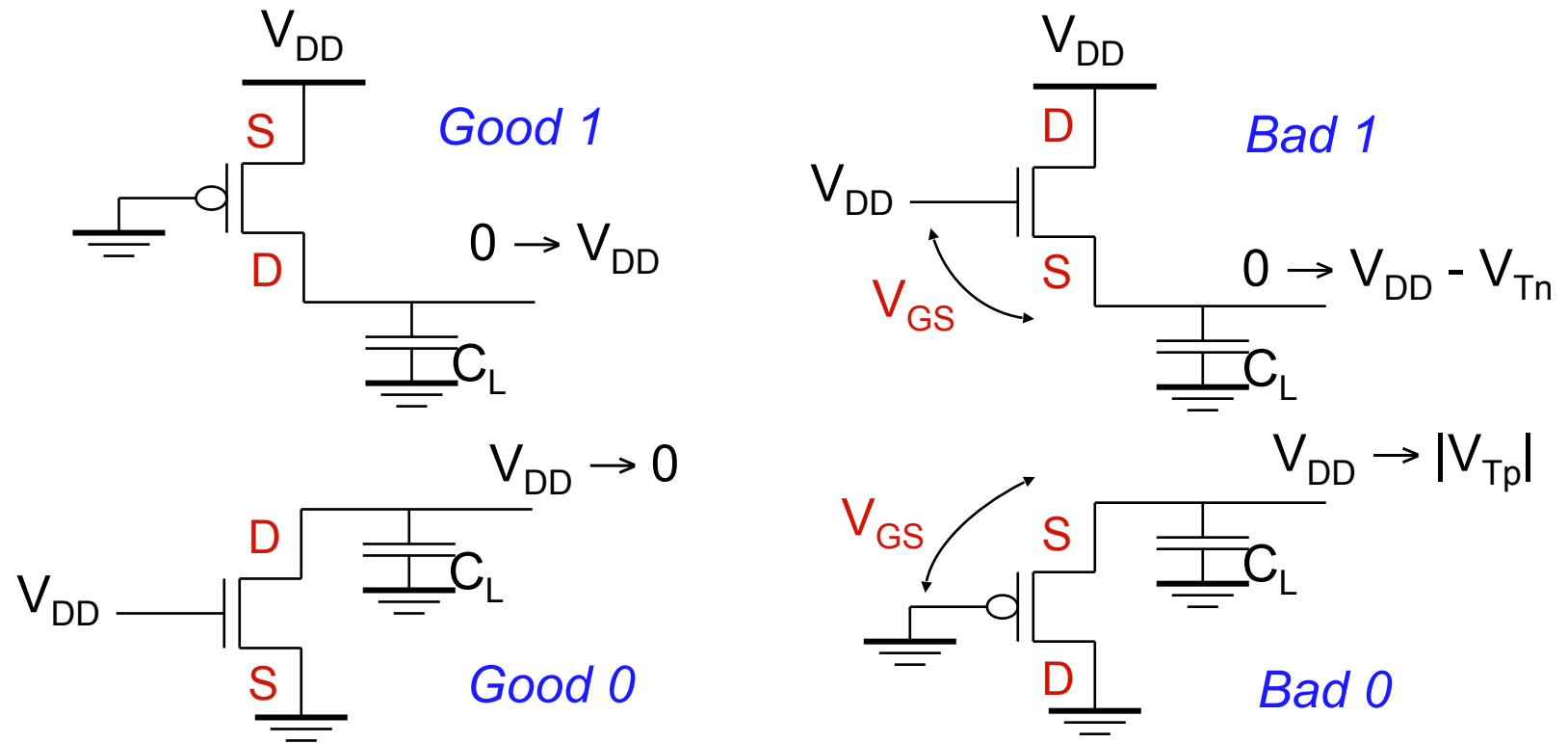
Non-inverting logic



*Why is this
a bad idea?*

PUN and PDN are **dual** logic networks
PUN and PDN functions are **complementary**

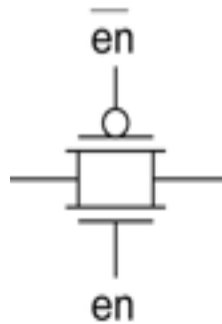
Switch Limitations



Tough luck ...

Transmission Gate

- ❑ Transmission gates are the way to build “switches” in CMOS.
- ❑ In general, both transistor types are needed:
 - ❑ nFET to pass zeros.
 - ❑ pFET to pass ones.
- ❑ The transmission gate is bi-directional (unlike logic gates).

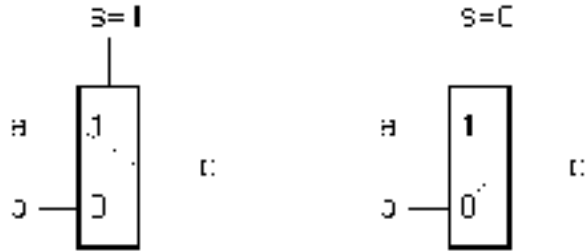


- ❑ Does not directly connect to V_{dd} and GND, but can be combined with logic gates or buffers to simplify many logic structures.

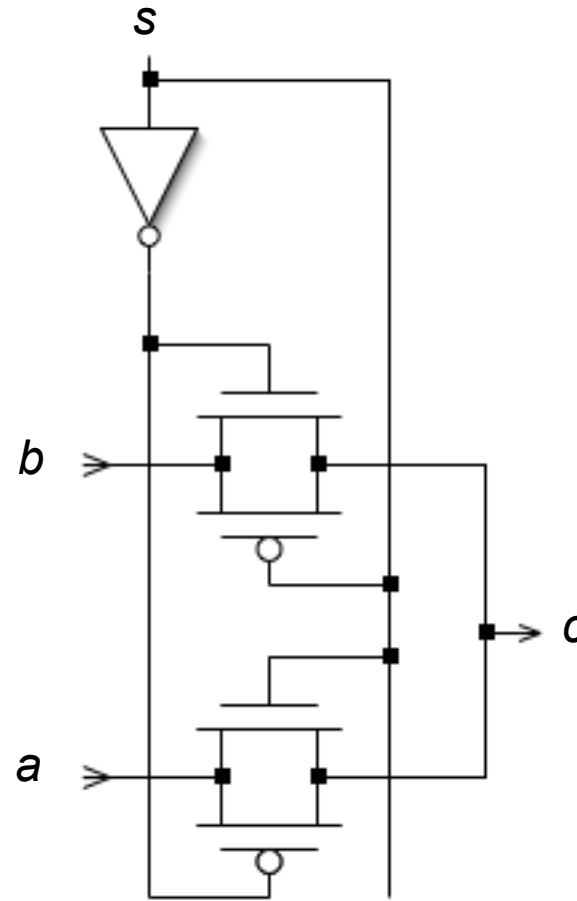
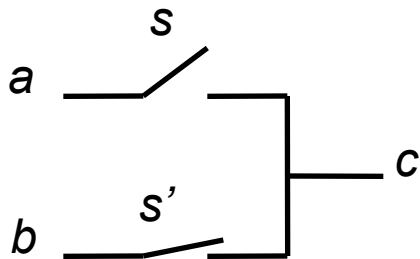
Transmission-gate Multiplexor

2-to-1 multiplexor:

$$c = sa + s'b$$

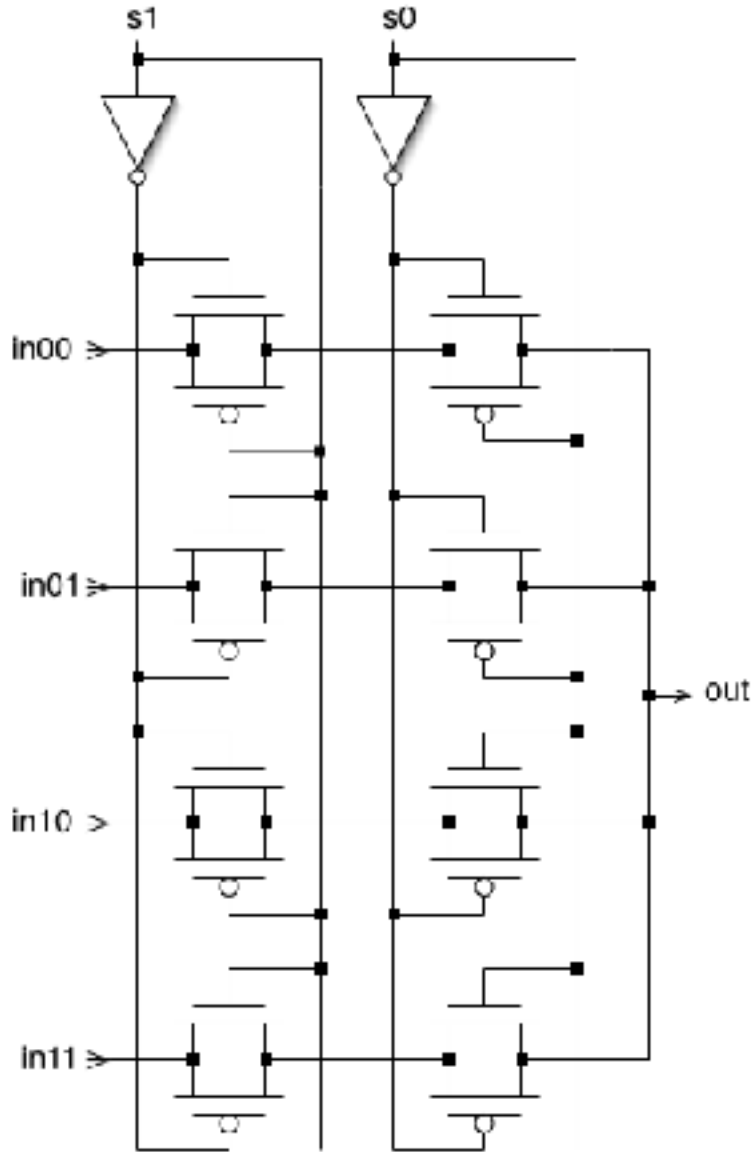


Switches simplify the implementation:



Compare the cost to logic gate implementation.

4-to-1 Transmission-gate Mux

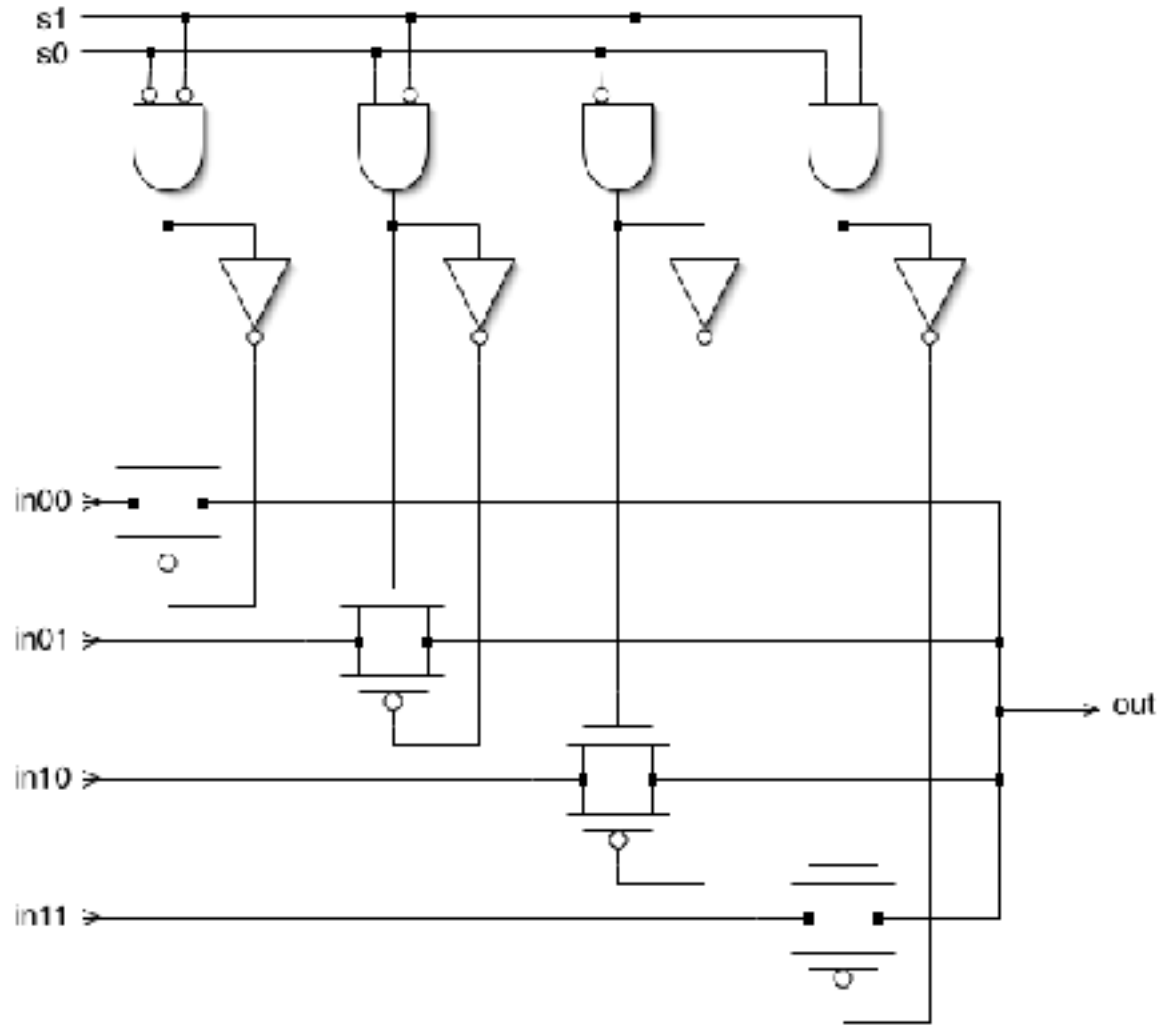


- The series connection of pass-transistors in each branch effectively forms the AND of $s1$ and $s0$ (or their complement).
- Compare cost to logic gate implementation

Any better solutions?

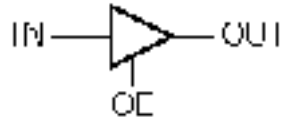
Alternative 4-to-1 Multiplexor

- This version has less delay from in to out.
- In both versions, care must be taken to avoid turning on multiple paths simultaneously (shorting together the inputs).



Tri-state Buffers

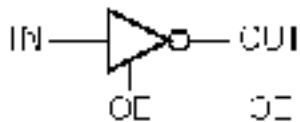
Tri-state Buffer:



| OE | IN | OUT |
|----|----|-----|
| 0 | 0 | Z |
| 0 | 1 | Z |
| 1 | 0 | 0 |
| 1 | 1 | 1 |

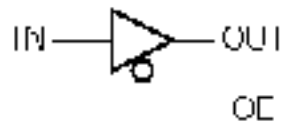
“high impedance” (output disconnected)

Variations:



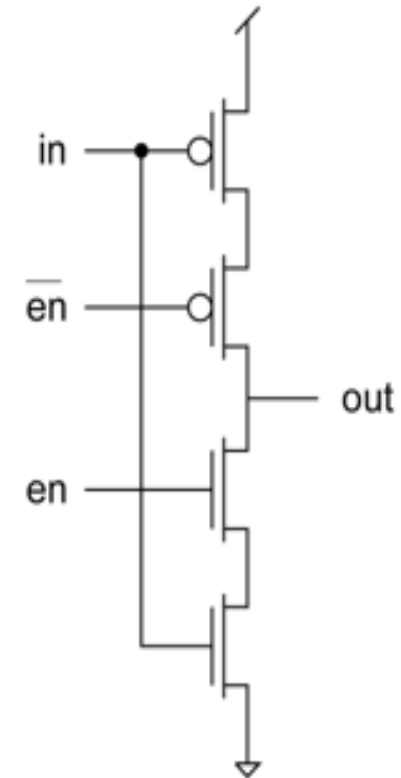
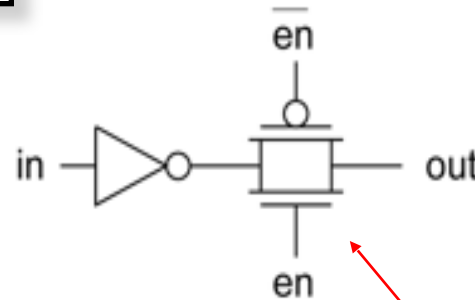
| OE | IN | OUT |
|----|----|-----|
| 0 | - | Z |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

Inverting buffer



| OE | IN | OUT |
|----|----|-----|
| 0 | 0 | 0 |
| 0 | 1 | 1 |
| 1 | - | Z |

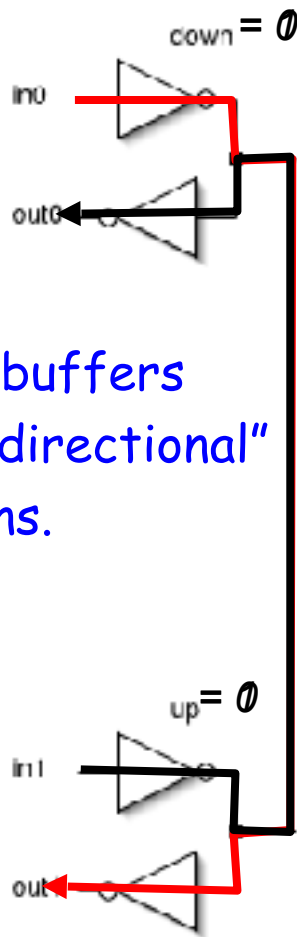
Inverted enable



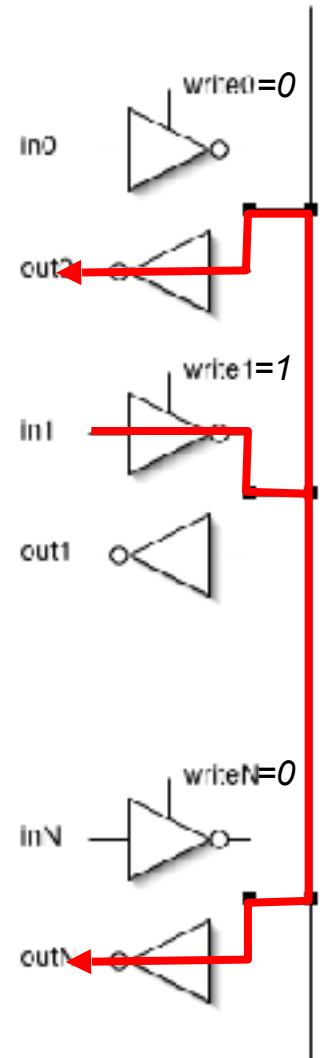
transmission gate useful in implementation

Tri-state Buffers

Tri-state buffers enable "bidirectional" connections.

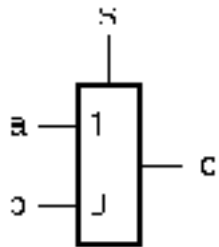


Tri-state buffers are used when multiple circuits all connect to a common wire. Only one circuit at a time is allowed to drive the bus. All others "disconnect" their outputs, but can "listen".

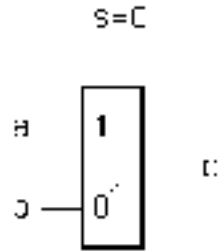
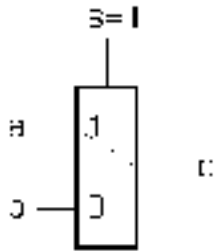


Tri-state Based Multiplexor

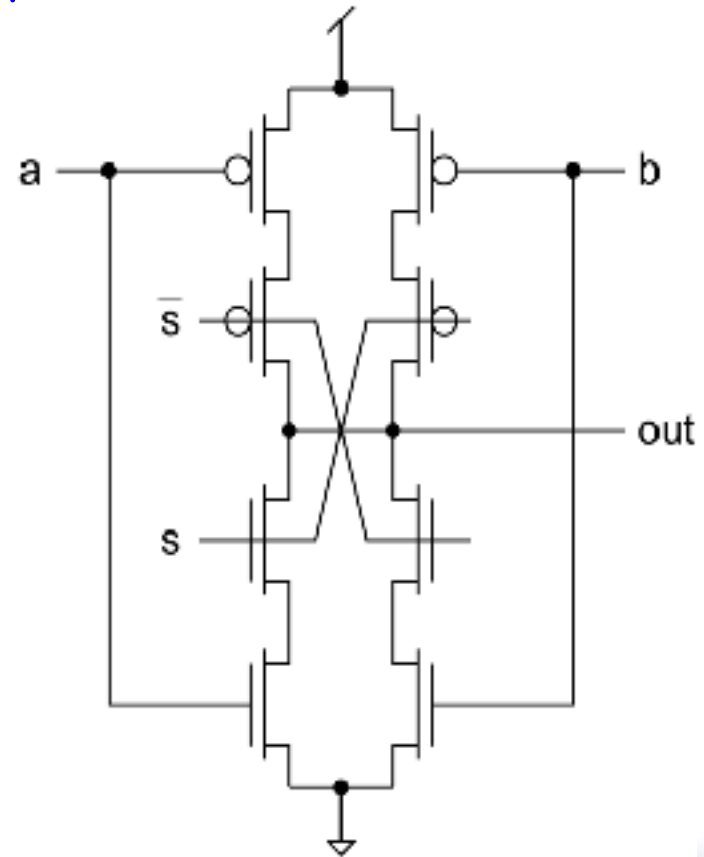
Multiplexor



If $s=1$ then $c=a$ else $c=b$

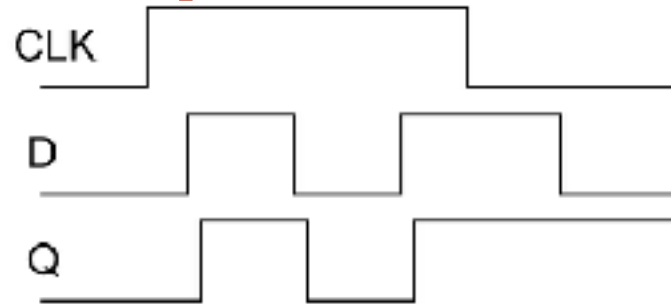
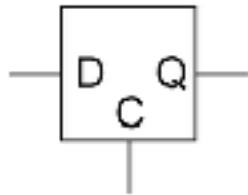


Transistor Circuit for inverting multiplexor:

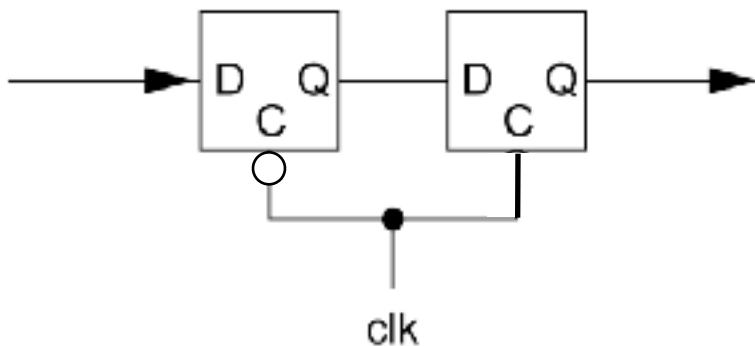


Latches and Flip-flops

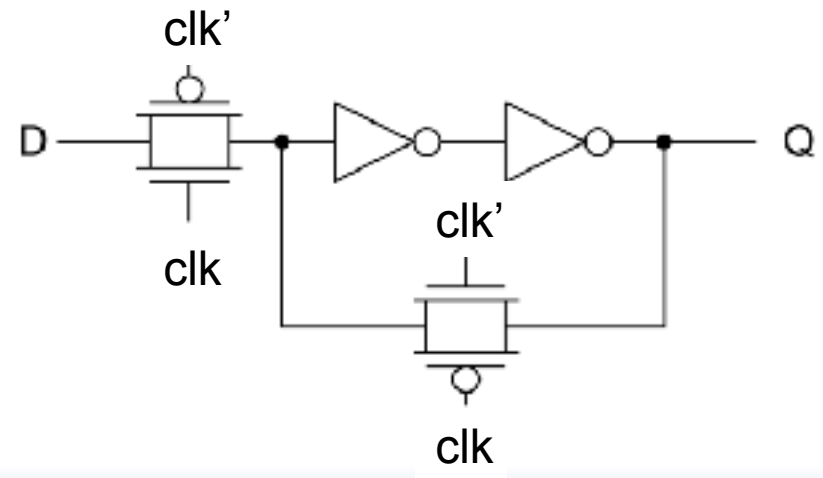
Positive Level-sensitive *latch*:



Positive Edge-triggered **flip-flop**
built from two level-sensitive
latches:



Latch Implementation:



Summary:

Complimentary CMOS Properties

- ❑ Full rail-to-rail swing
- ❑ Symmetrical VTC
- ❑ No (...) static power dissipation
- ❑ Direct path current during switching



Digital abstraction

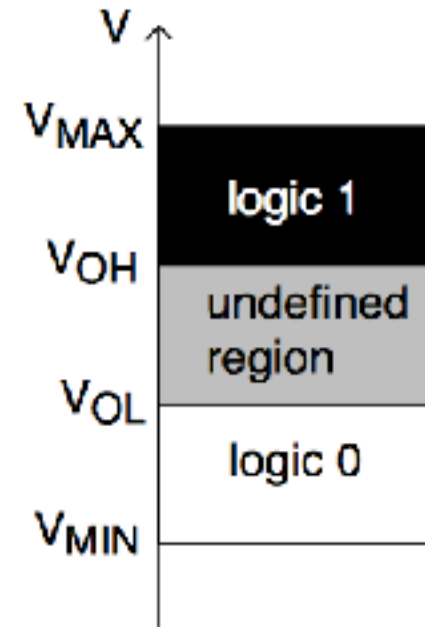
Noise and Digital Systems

- ❑ Circuit needs to work despite “analog” noise
 - Digital gates can and must reject noise
 - This is actually how digital systems are defined

- ❑ Digital system is one where:
 - Discrete values mapped to analog levels and back
 - Elements (gates) can reject noise
 - For “small” amounts of noise, output noise is less than input noise
 - Thus, for sufficiently “small” noise, the system acts as if it was noiseless
 - This is called **regeneration**

Bridging the digital and the analog worlds

- How to represent 0's and 1's in a world that is analog?



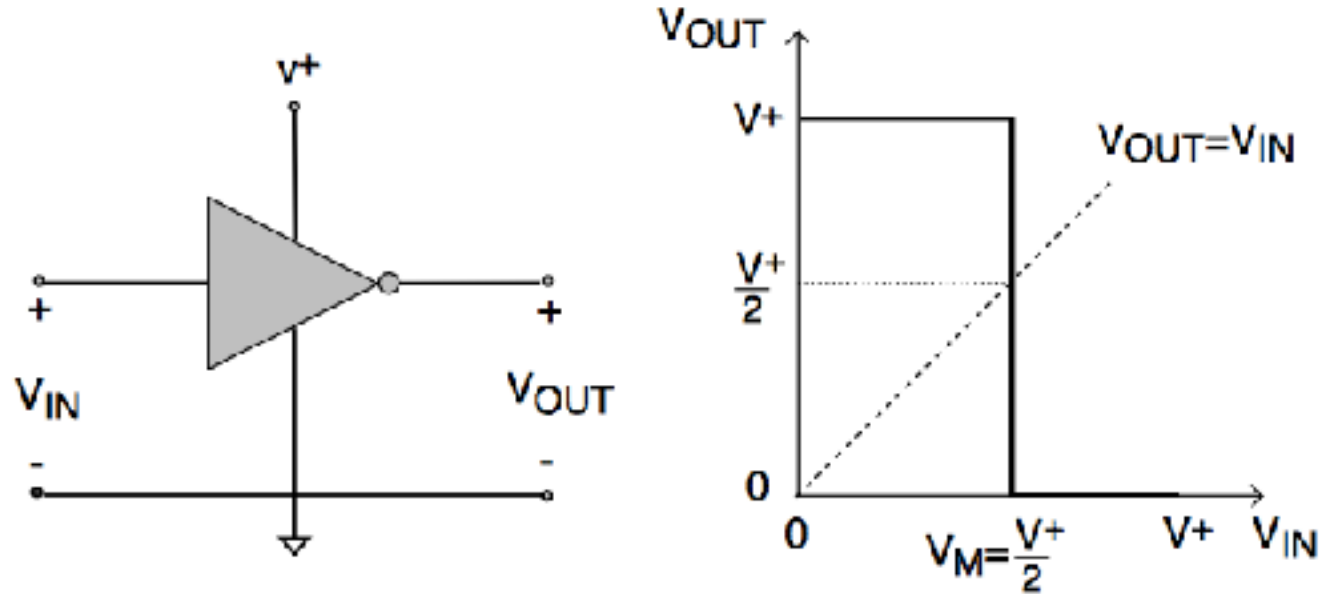
The Static Definition

- **Logic 0:** $V_{MIN} \leq V \leq V_{OL}$
- **Logic 1:** $V_{OH} \leq V \leq V_{MAX}$
- **Undefined logic value:** $V_{OL} \leq V \leq V_{OH}$



Ideal Inverter

Circuit representation and ideal transfer function:



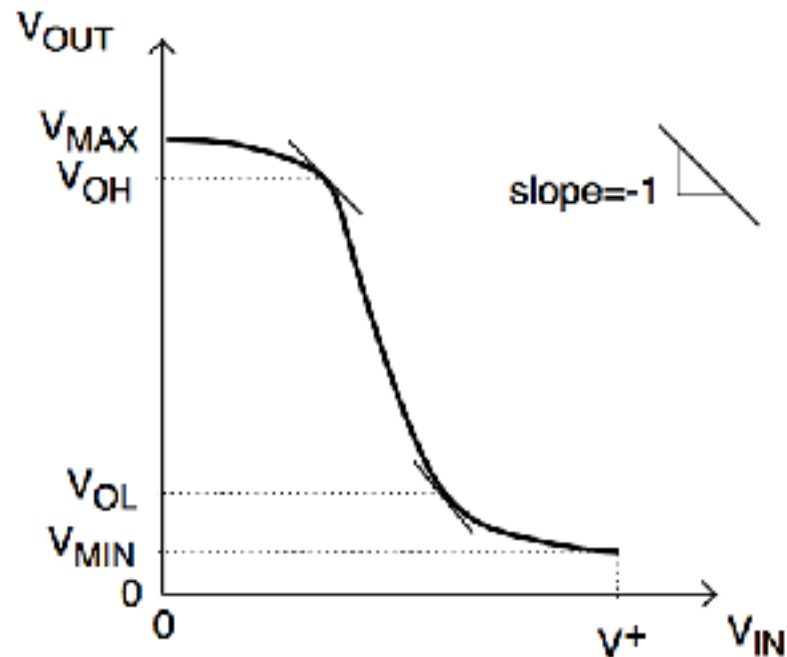
Define *switching point* or *logic threshold* :

- $V_M \equiv$ input voltage for which $V_{OUT} = V_{IN}$
 - For $0 \leq V_{IN} < V_M \Rightarrow V_{OUT} = V^+$
 - For $V_M < V_{IN} \leq V^+ \Rightarrow V_{OUT} = 0$

Ideal inverter returns well defined logical outputs (0 or V^+) even in the presence of considerable noise in V_{IN} (from voltage spikes, crosstalk, etc.)

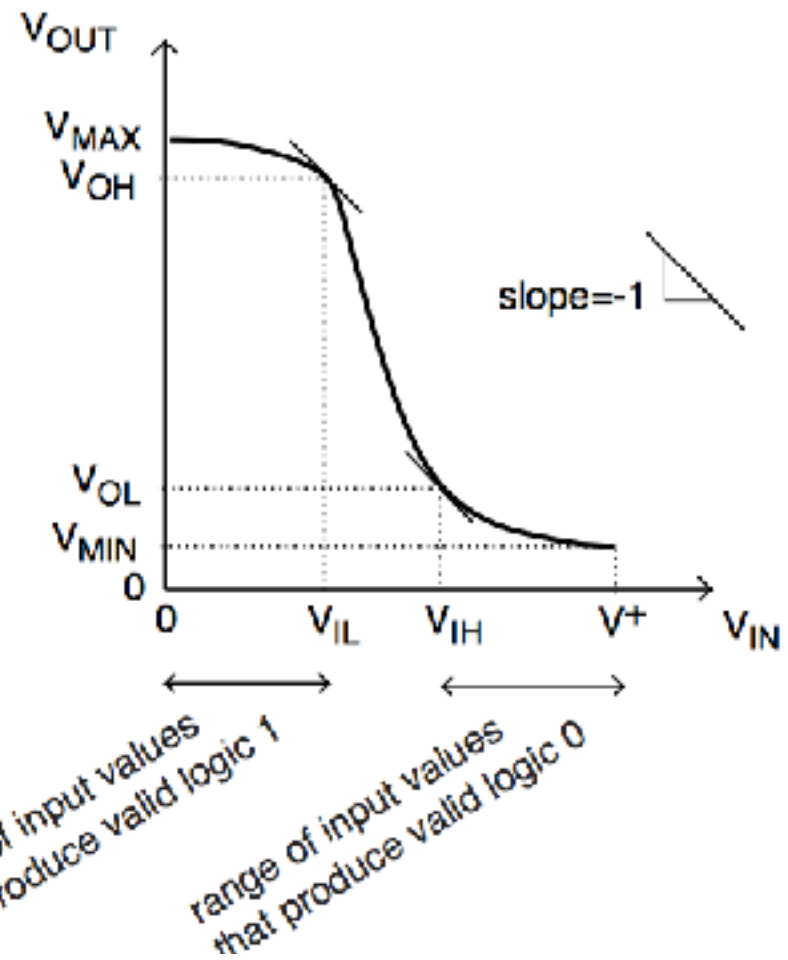
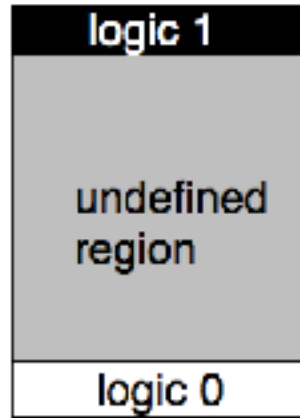
\Rightarrow signal is *regenerated*!

“Real Inverter”



- Logic 0:
 - $V_{MIN} \equiv$ output voltage for which $V_{IN} = V^+$
 - $V_{OL} \equiv$ smallest output voltage where slope = -1
- Logic 1:
 - $V_{OH} \equiv$ largest output voltage where slope = -1
 - $V_{MAX} \equiv$ output voltage for which $V_{IN} = 0$

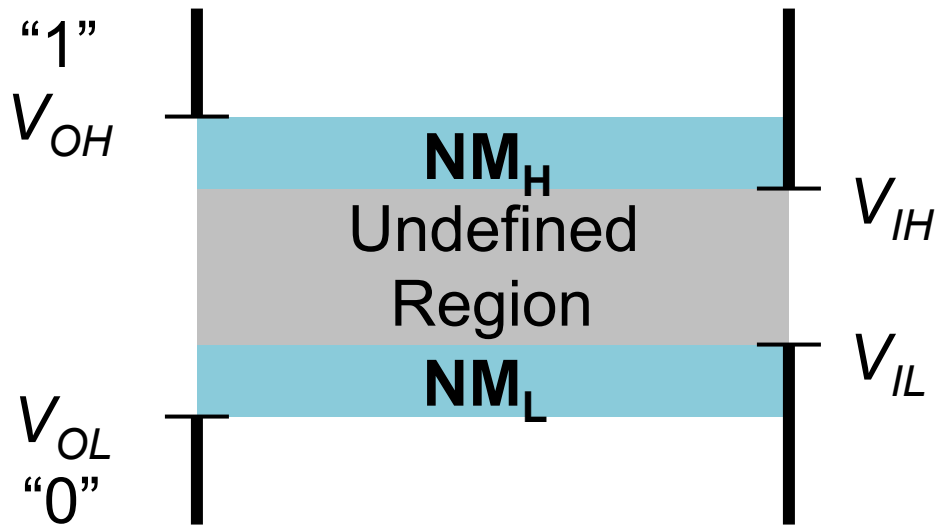
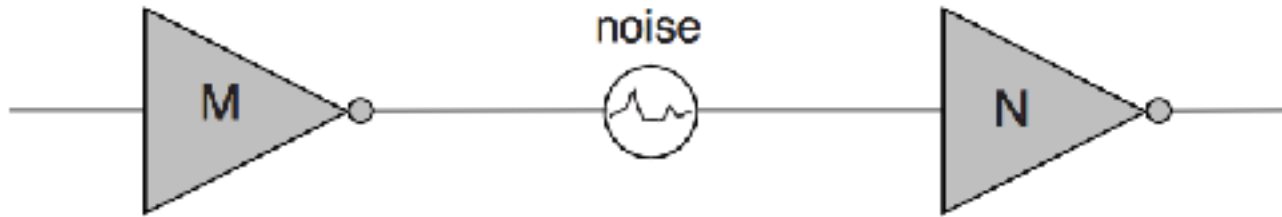
Valid Input Ranges



If range of output values V_{OL} to V_{OH} is *wider* than the range of input values V_{IL} to V_{IH} , then the inverter exhibits some noise immunity. (Voltage gain > 1)

Quantify this through *noise margins*.

Definition of Noise Margins



Noise margin high:
 $NM_H = V_{OH} - V_{IH}$

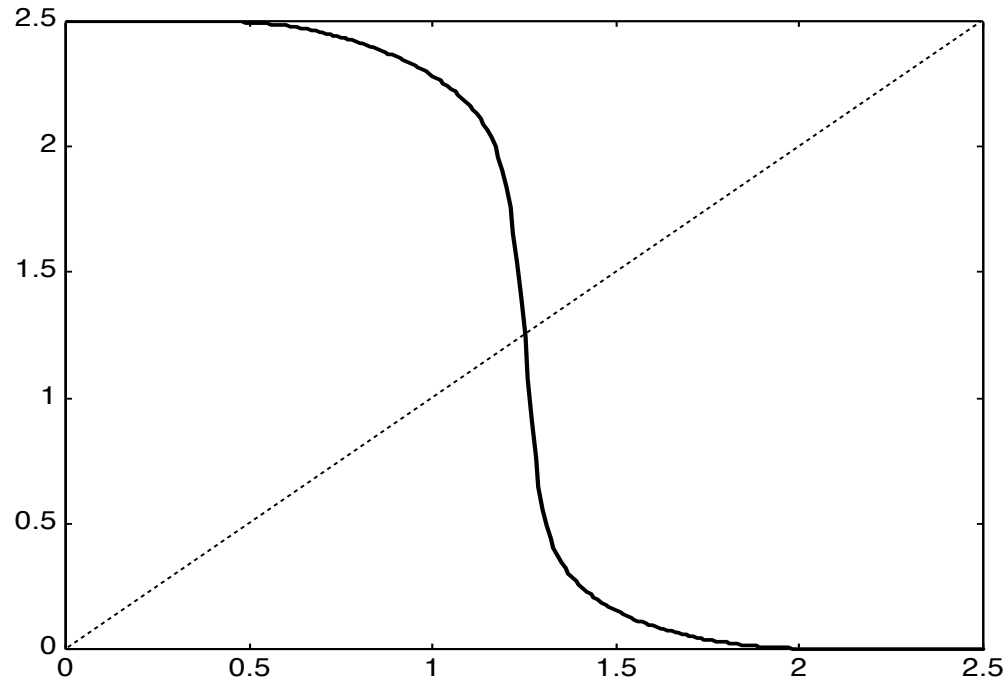
Noise margin low:
 $NM_L = V_{IL} - V_{OL}$

Gate
Output
(Stage M)



Gate
Input
(Stage M+1)

Simulated Inverter VTC (Spice)



$V_{OH} =$

$V_{OL} =$

$V_{IL} =$

$V_{IH} =$

$N_{MH} =$

$N_{ML} =$

$V_M =$